

## N-Channel 200-V (D-S) MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
200	0.130 at V <sub>GS</sub> = 10 V	3
	0.142 at V <sub>GS</sub> = 6.0 V	2.8

### FEATURES

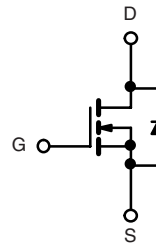
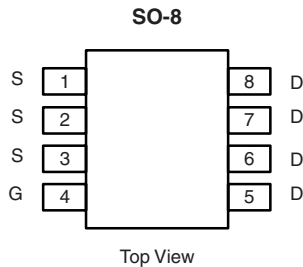
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> Tested

### APPLICATIONS

- Primary Side Switch



RoHS\*  
COMPLIANT



N-Channel MOSFET

Ordering Information: Si4418DY-E3  
Si4418DY-T1-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted					
Parameter	Symbol	10 sec	Steady State	Unit	
Drain-Source Voltage	V <sub>DS</sub>	200		V	
Gate-Source Voltage	V <sub>GS</sub>	± 20			
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	I <sub>D</sub>	T <sub>A</sub> = 25 °C	3	2.3	A
		T <sub>A</sub> = 85 °C	2.1	1.6	
Pulsed Drain Current	I <sub>DM</sub>	12			
Avalanche Current	I <sub>AS</sub>	6			
Single Avalanche Energy (Duty Cycle ≤ 1 %)	E <sub>AS</sub>	1.8		mJ	
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	2.1	1.25	A	
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	T <sub>A</sub> = 25 °C	2.5	1.5	W
		T <sub>A</sub> = 85 °C	1.3	0.8	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	t ≤ 10 sec	36	50	°C/W
		Steady State	71	85	
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	15	20		

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

\* Pb containing terminations are not RoHS compliant, exemptions may apply.



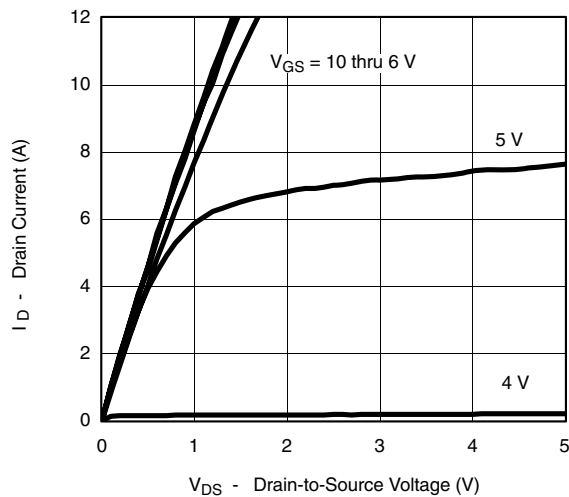
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2		4	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 20\ \text{V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 200\ \text{V}, V_{GS} = 0\ \text{V}$			1	$\mu\text{A}$
		$V_{DS} = 200\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 85\text{ }^\circ\text{C}$			20	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}, V_{GS} = 10\ \text{V}$	12			A
Drain-Source On-State Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = 10\ \text{V}, I_D = 3\ \text{A}$		0.110	0.130	$\Omega$
		$V_{GS} = 6.0\ \text{V}, I_D = 2.8\ \text{A}$		0.120	0.142	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\ \text{V}, I_D = 3\ \text{A}$		13		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 2.1\ \text{A}, V_{GS} = 0\ \text{V}$		0.8	1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = 100\ \text{V}, V_{GS} = 10\ \text{V}, I_D = 3\ \text{A}$		20	30	nC
Gate-Source Charge	$Q_{gs}$			4.5		
Gate-Drain Charge	$Q_{gd}$			6.5		
Gate Resistance	$R_g$	$f = 1\ \text{MHz}$	1	2	3.4	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 100\ \text{V}, R_L = 100\ \Omega$ $I_D \cong 1\ \text{A}, V_{GEN} = 10\ \text{V}, R_G = 6\ \Omega$		15	25	ns
Rise Time	$t_r$			15	25	
Turn-Off Delay Time	$t_{d(off)}$			40	60	
Fall Time	$t_f$			20	30	
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 2.1\ \text{A}, di/dt = 100\ \text{A}/\mu\text{s}$		70	110	

Notes:

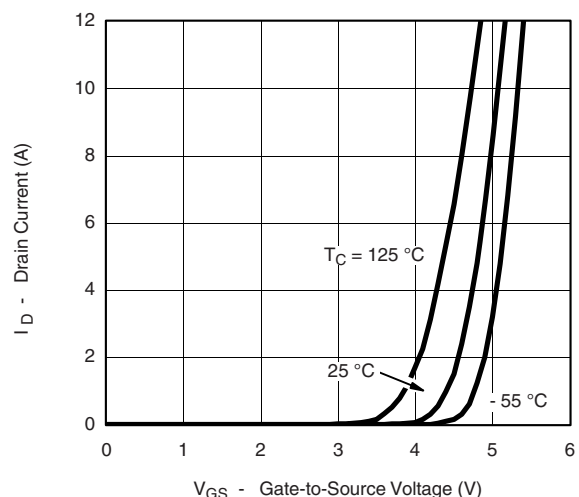
- a. Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS**  $25\text{ }^\circ\text{C}$ , unless otherwise noted

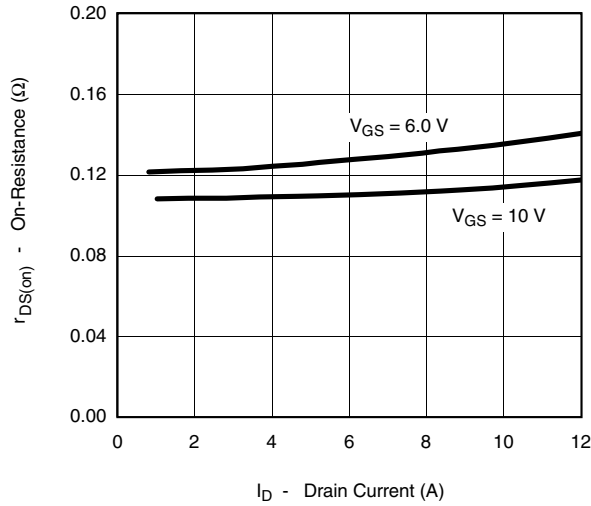


Output Characteristics

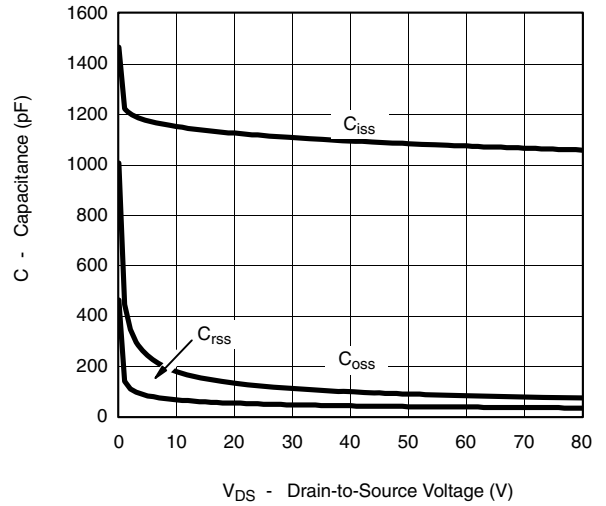


Transfer Characteristics

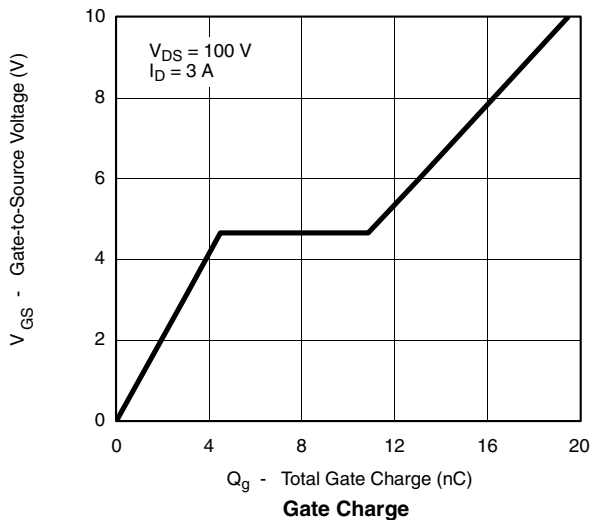
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



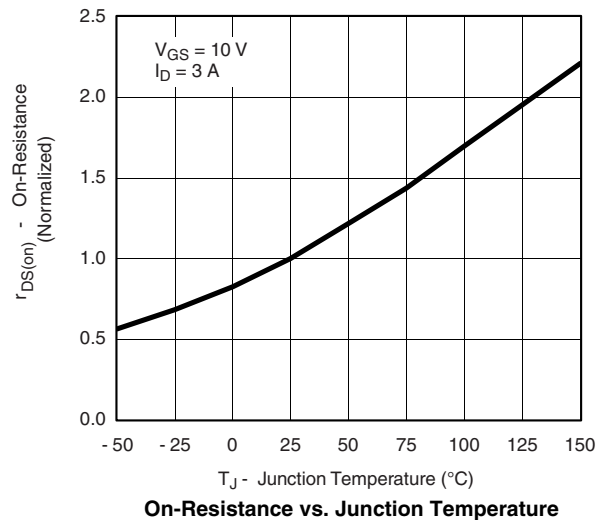
**On-Resistance vs. Drain Current**



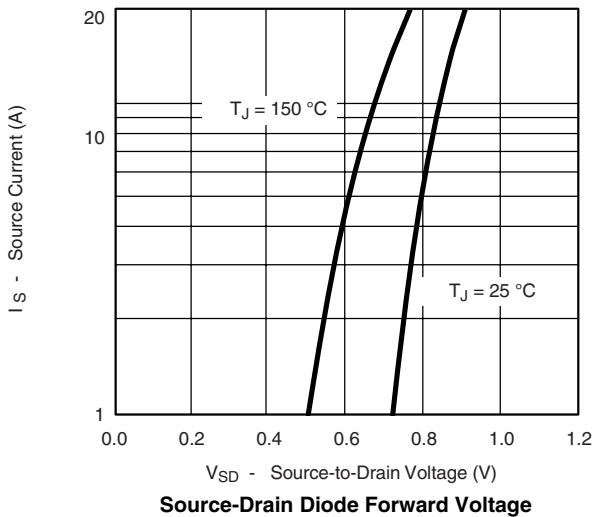
**Capacitance**



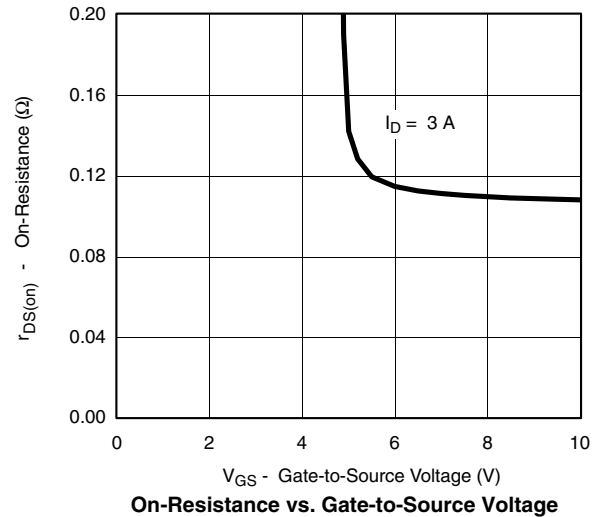
**Gate Charge**



**On-Resistance vs. Junction Temperature**



**Source-Drain Diode Forward Voltage**



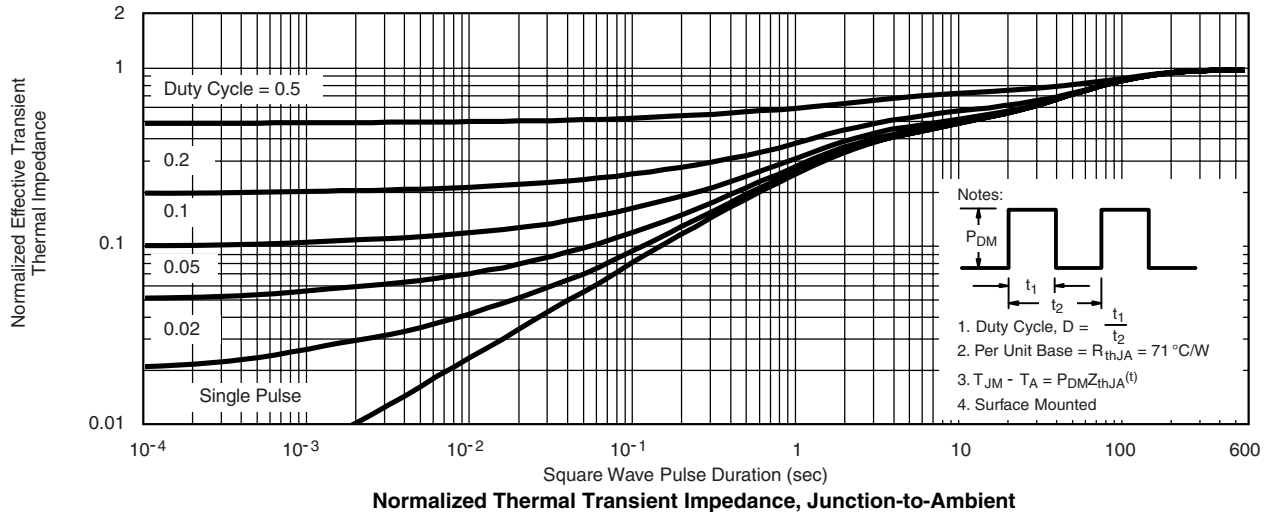
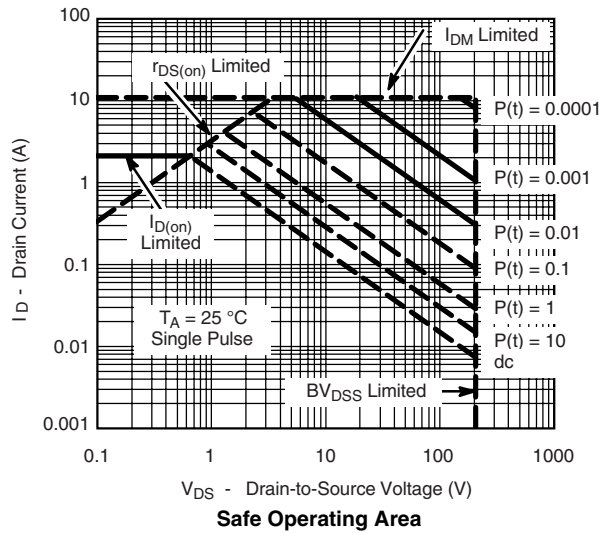
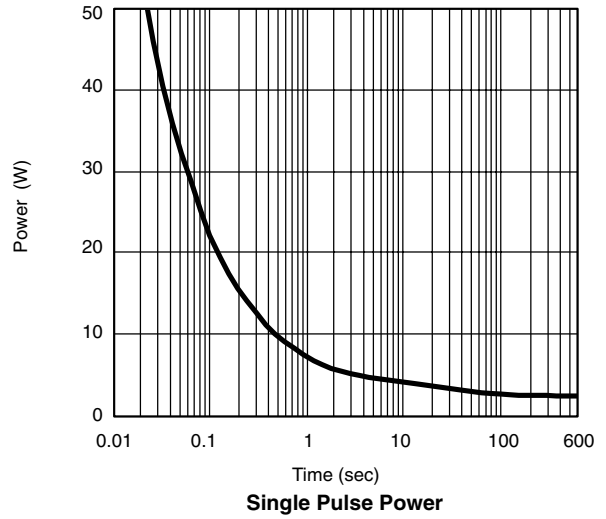
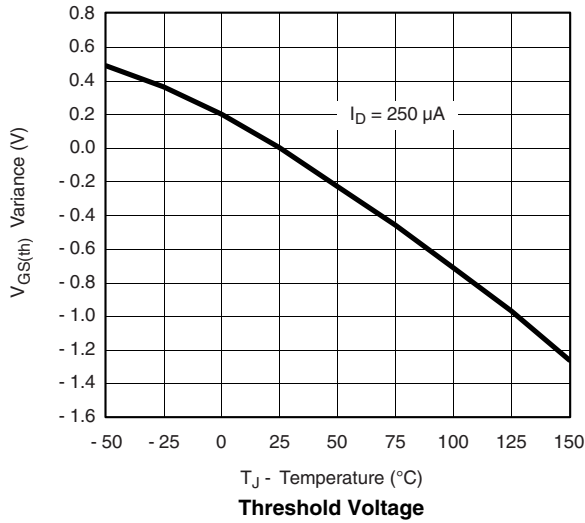
**On-Resistance vs. Gate-to-Source Voltage**

# Si4418DY

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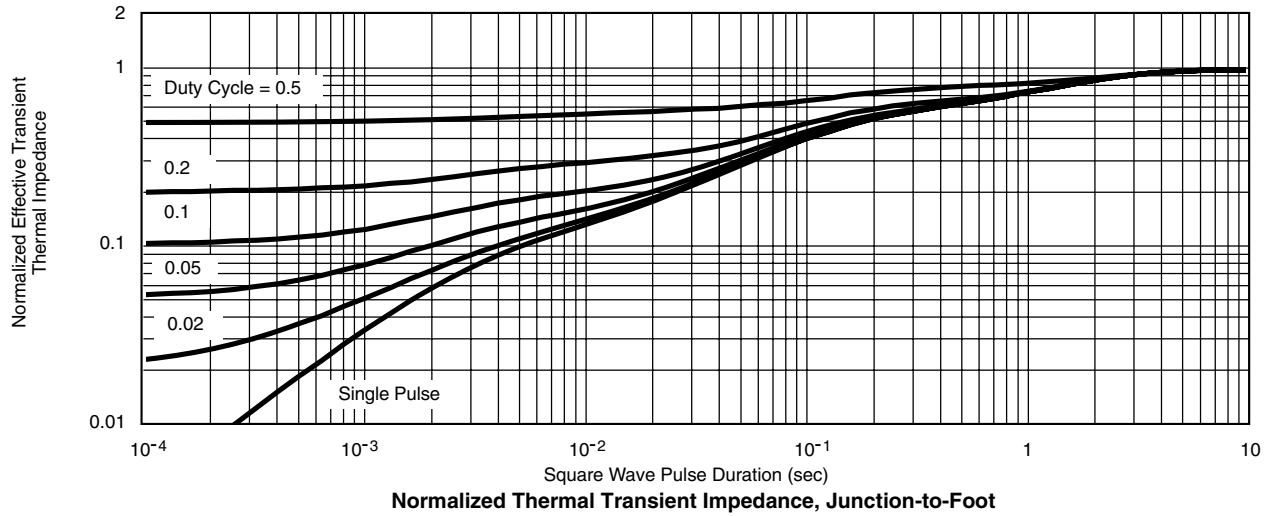


## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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